

GAL18V10

High Performance E²CMOS PLD Generic Array Logic™

FEATURES

- HIGH PERFORMANCE E²CMOS[®] TECHNOLOGY
- 7.5 ns Maximum Propagation Delay
- Fmax = 111 MHz
- 5.5 ns Maximum from Clock Input to Data Output
- TTL Compatible 16 mA Outputs
- UltraMOS® Advanced CMOS Technology
- LOW POWER CMOS
 - 75 mA Typical Icc
- ACTIVE PULL-UPS ON ALL PINS
- E² CELL TECHNOLOGY
 - Reconfigurable Logic
 - Reprogrammable Cells
 - 100% Tested/100% Yields
 - High Speed Electrical Erasure (<100ms)
 - 20 Year Data Retention
- TEN OUTPUT LOGIC MACROCELLS
 - Uses Standard 22V10 Macrocell Architecture
 - Maximum Flexibility for Complex Logic Designs
- PRELOAD AND POWER-ON RESET OF REGISTERS
 - 100% Functional Testability
- APPLICATIONS INCLUDE:
 - DMA Control
 - State Machine Control
 - High Speed Graphics Processing
 - Standard Logic Speed Upgrade
- ELECTRONIC SIGNATURE FOR IDENTIFICATION

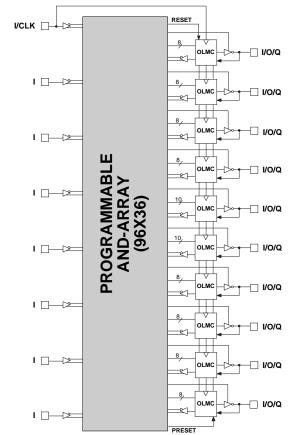
DESCRIPTION

The GAL18V10, at 7.5 ns maximum propagation delay time, combines a high performance CMOS process with Electrically Erasable (E^2) floating gate technology to provide a very flexible 20-pin PLD. CMOS circuitry allows the GAL18V10 to consume much less power when compared to its bipolar counterparts. The E^2 technology offers high speed (<100ms) erase times, providing the ability to reprogram or reconfigure the device quickly and efficiently.

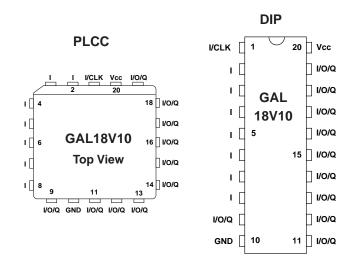
By building on the popular 22V10 architecture, the GAL18V10 eliminates the learning curve usually associated with using a new device architecture. The generic architecture provides maximum design flexibility by allowing the Output Logic Macrocell (OLMC) to be configured by the user. The GAL18V10 OLMC is fully compatible with the OLMC in standard bipolar and CMOS 22V10 devices.

Unique test circuitry and reprogrammable cells allow complete AC, DC, and functional testing during manufacture. As a result, Lattice Semiconductor delivers 100% field programmability and functionality of all GAL products. In addition, 100 erase/write cycles and data retention in excess of 20 years are specified.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



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July 1997

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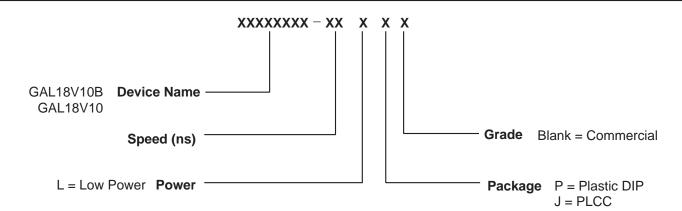


GAL18V10 ORDERING INFORMATION

Commercial Grade Specifications

Tpd (ns)	Tsu (ns)	Tco (ns)	Icc (mA)	Ordering #	Package
7.5	6	5.5	115	GAL18V10B-7LP	20-Pin Plastic DIP
			115	GAL18V10B-7LJ	20-Lead PLCC
10	7	7	115	GAL18V10B-10LP	20-Pin Plastic DIP
			115	GAL18V10B-10LJ	20-Lead PLCC
15	8	10	115	GAL18V10B-15LP	20-Pin Plastic DIP
			115	GAL18V10B-15LJ	20-Lead PLCC
			115	GAL18V10-15LP	20-Pin Plastic DIP
			115	GAL18V10-15LJ	20-Lead PLCC
20	12	12	115	GAL18V10B-20LP	20-Pin Plastic DIP
			115	GAL18V10B-20LJ	20-Lead PLCC
			115	GAL18V10-20LP	20-Pin Plastic DIP
			115	GAL18V10-20LJ	20-Lead PLCC

PART NUMBER DESCRIPTION





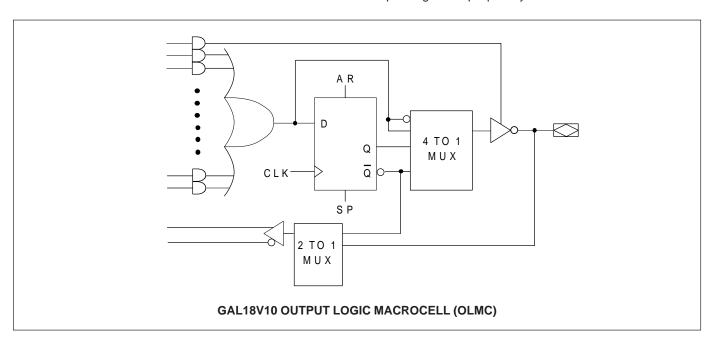
OUTPUT LOGIC MACROCELL (OLMC)

The GAL18V10 has a variable number of product terms per OLMC. Of the ten available OLMCs, two OLMCs have access to ten product terms (pins 14 and 15), and the other eight OLMCs have eight product terms each. In addition to the product terms available for logic, each OLMC has an additional product-term dedicated to output enable control.

The output polarity of each OLMC can be individually programmed to be true or inverting, in either combinatorial or registered mode. This allows each output to be individually configured as either active high or active low.

The GAL18V10 has a product term for Asynchronous Reset (AR) and a product term for Synchronous Preset (SP). These two product terms are common to all registered OLMCs. The Asynchronous Reset sets all registered outputs to zero any time this dedicated product term is asserted. The Synchronous Preset sets all registers to a logic one on the rising edge of the next clock pulse after this product term is asserted.

NOTE: The AR and SP product terms will force the Q output of the flip-flop into the same state regardless of the polarity of the output. Therefore, a reset operation, which sets the register output to a zero, may result in either a high or low at the output pin, depending on the pin polarity chosen.



OUTPUT LOGIC MACROCELL CONFIGURATIONS

Each of the Macrocells of the GAL18V10 has two primary functional modes: registered, and combinatorial I/O. The modes and the output polarity are set by two bits (SO and S1), which are normally controlled by the logic compiler. Each of these two primary modes, and the bit settings required to enable them, are described below and on the the following page.

REGISTERED

In registered mode the output pin associated with an individual OLMC is driven by the Q output of that OLMC's D-type flip-flop. Logic polarity of the output signal at the pin may be selected by specifying that the output buffer drive either true (active high) or inverted (active low). Output tri-state control is available as an individual product term for each OLMC, and can therefore be defined by a logic equation. The D flip-flop's /Q output is fed back into the AND array, with both the true and complement of the feedback available as inputs to the AND array.

NOTE: In registered mode, the feedback is from the /Q output of the register, and not from the pin; therefore, a pin defined as registered is an output only, and cannot be used for dynamic I/O, as can the combinatorial pins.

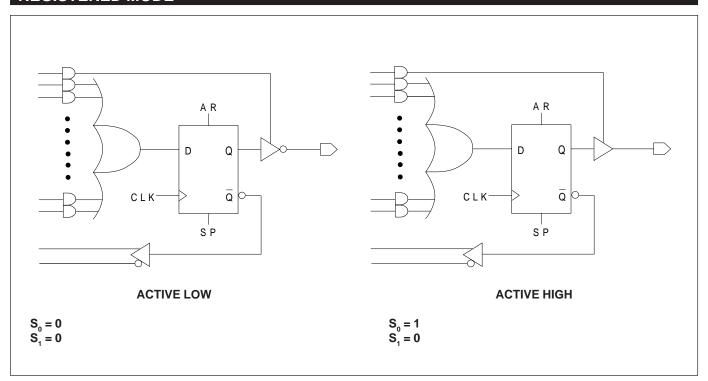
COMBINATORIAL I/O

In combinatorial mode the pin associated with an individual OLMC is driven by the output of the sum term gate. Logic polarity of the output signal at the pin may be selected by specifying that the output buffer drive either true (active high) or inverted (active low). Output tri-state control is available as an individual product-term for each output, and may be individually set by the compiler as either "on" (dedicated output), "off" (dedicated input), or "product-term driven" (dynamic I/O). Feedback into the AND array is from the pin side of the output enable buffer. Both polarities (true and inverted) of the pin are fed back into the AND array.

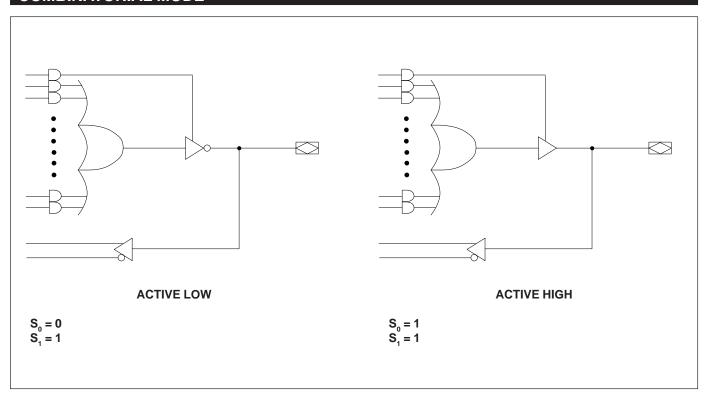




REGISTERED MODE



COMBINATORIAL MODE





GAL18V10 LOGIC DIAGRAM / JEDEC FUSE MAP **DIP and PLCC Package Pinouts** ASYNCHRONOUS RESET 0000 (TO ALL REGISTERS) 0036 8 **OLMC** 19 S0 3456 S1 3457 0324 0360 8 **OLMC** 18 S0 3458 0648 2 — 🔀 3459 0684 8 **OLMC** 17 SO 3460 0972 S1 3461 3 — 🔀 1008 **OLMC** 16 S0 3462 1296 \$1 3463 1332 10 **OLMC** 15 S0 3464 S1 3465 1692 5 — 🔀 1728 10 OLMC 14 S0 3466 S1 3467 2088 6 —>= 2124 OLMC 13 S0 3468 S1 3469 2412 7 —>= 2448 OLMC 12 S0 3470 S1 3471 2736 8 —>= OLMC 11 S0 3472 3060 S1 3473 3096 8 **OLMC** 9 S0 3474 S1 3475 3384 3420 SYNCHRONOUS PRESET (TO ALL REGISTERS)

3476, 3477 ...

Electronic Signature Byte 7 Byte 6 Byte 5 Byte 4 Byte 3 Byte 2 Byte 1 Byte 0



ABSOLUTE MAXIMUM RATINGS(1)

Supply voltage V _{CC}	0.5 to +7V
Input voltage applied	2.5 to V _{cc} +1.0V
Off-state output voltage applied	2.5 to V _{cc} +1.0V
Storage Temperature	65 to 150°C
Ambient Temperature with	
D A P J	FF 1: 40F0O

Power Applied-55 to 125°C

1. Stresses above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress only ratings and functional operation of the device at these or at any other conditions above those indicated in the operational sections of this specification is not implied (while programming, follow the programming specifications).

RECOMMENDED OPERATING COND.

Commercial Devices:

Ambient Temperature (T _A)	0 to +75°C
Supply voltage (V _{CC})	
with Respect to Ground	+4.75 to +5.25V

DC ELECTRICAL CHARACTERISTICS

Over Recommended Operating Conditions (Unless Otherwise Specified)

PARAMETER	CONDITION	MIN.	TYP.3	MAX.	UNITS
Input Low Voltage		Vss - 0.5	_	0.8	V
Input High Voltage		2.0	_	Vcc+1	V
Input or I/O Low Leakage Current	$0V \le V_{IN} \le V_{IL}$ (MAX.)		_	-100	μΑ
Input or I/O High Leakage Current	$3.5 \text{V} \leq \text{V}_{\text{IN}} \leq \text{V}_{\text{CC}}$	_	_	10	μΑ
Output Low Voltage	$I_{OL} = MAX$. $Vin = V_{IL} \text{ or } V_{IH}$	_	_	0.5	V
Output High Voltage	$I_{OH} = MAX$. $Vin = V_{IL}$ or V_{IH}	2.4	_	_	V
Low Level Output Current		_	_	16	mA
High Level Output Current		-	_	-3.2	mA
Output Short Circuit Current	V cc = 5V V out = 0.5V Ta = 25°C	-30	_	-130	mA
	Input Low Voltage Input High Voltage Input or I/O Low Leakage Current Input or I/O High Leakage Current Output Low Voltage Output High Voltage Low Level Output Current High Level Output Current	Input Low Voltage Input High Voltage Input or I/O Low Leakage Current OV ≤ V _{IN} ≤ V _{IL} (MAX.) Input or I/O High Leakage Current 3.5V ≤ V _{IN} ≤ V _{CC} Output Low Voltage IoL = MAX. Vin = V _{IL} or V _{IH} Output High Voltage IoH = MAX. Vin = V _{IL} or V _{IH} Low Level Output Current High Level Output Current	Input Low Voltage Vss − 0.5 Input High Voltage 2.0 Input or I/O Low Leakage Current $0V \le V_{IN} \le V_{IL}$ (MAX.) — Input or I/O High Leakage Current $3.5V \le V_{IN} \le V_{CC}$ — Output Low Voltage $I_{OL} = MAX$. $V_{ID} = V_{IL}$ or V_{IH} — Output High Voltage $I_{OH} = MAX$. $V_{ID} = V_{IL}$ or V_{IH} 2.4 Low Level Output Current — High Level Output Current —	Input Low Voltage Vss − 0.5 — Input High Voltage 2.0 — Input or I/O Low Leakage Current $0V \le V_{IN} \le V_{IL}$ (MAX.) — — Input or I/O High Leakage Current $3.5V \le V_{IN} \le V_{CC}$ — — Output Low Voltage IoL = MAX. Vin = VIL or VIH — — Output High Voltage IoH = MAX. Vin = VIL or VIH 2.4 — Low Level Output Current — — — High Level Output Current — — —	Input Low Voltage Vss - 0.5 — 0.8 Input High Voltage 2.0 — Vcc+1 Input or I/O Low Leakage Current 0V ≤ VIN ≤ VIL (MAX.) — — — 100 Input or I/O High Leakage Current 3.5V ≤ VIN ≤ Vcc — — 10 Output Low Voltage IoL = MAX. Vin = VIL or VIH — — 0.5 Output High Voltage IoH = MAX. Vin = VIL or VIH 2.4 — — Low Level Output Current — — — — — High Level Output Current — — — — — —

COMMERCIAL

Icc	Operating Power	V IL = 0.5V V IH = 3.0V	L -7/-10/-15/-20	_	75	115	mA
	Supply Current	f _{toggle} = 15MHz Outputs Open					

¹⁾ The leakage current is due to the internal pull-up on all pins. See **Input Buffer** section for more information.

²⁾ One output at a time for a maximum duration of one second. Vout = 0.5V was selected to avoid test problems caused by tester ground degradation. Characterized but not 100% tested.

³⁾ Typical values are at Vcc = 5V and TA = 25 °C

AC SWITCHING CHARACTERISTICS

Over Recommended Operating Conditions

			C	MC	C	MC	CC	MC	CC	MC	
DADAM	TEST	DESCRIPTION	-7		-10		-1	-15		0	UNITS
PARAM.	COND.1	COND.1		MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	UNITS
t pd	А	Input or I/O to Comb. Output	—	7.5	_	10	_	15	_	20	ns
t co	Α	Clock to Output Delay	_	5.5	_	7	_	10	_	12	ns
tcf ²	_	Clock to Feedback Delay	_	3.5	_	3.5	_	7	_	10	ns
t su		Setup Time, Input or Fdbk before Clk↑	5.5	_	6	_	8	_	12	_	ns
t h	_	Hold Time, Input or Fdbk after Clk↑	0	_	0	_	0	_	0	_	ns
	А	Maximum Clock Frequency with External Feedback, 1/(tsu + tco)	90.9	_	76.9	_	55.5	_	41.6	_	MHz
fmax ³	А	Maximum Clock Frequency with Internal Feedback, 1/(tsu + tcf)	111	_	105	_	66.7	_	45.4	_	MHz
	А	Maximum Clock Frequency with No Feedback	111	_	105	_	66.7	_	62.5	_	MHz
t wh	_	Clock Pulse Duration, High	4	_	4	_	6	_	8	_	ns
twl	_	Clock Pulse Duration, Low	4	_	4	_	6	_	8	_	ns
t en	В	Input or I/O to Output Enabled	_	8	_	10	_	15	_	20	ns
t dis	С	Input or I/O to Output Disabled	_	8	_	9	_	15	_	20	ns
t ar	А	Input or I/O to Asynch. Reset of Reg.	_	13	_	13	_	20	_	20	ns
t arw	_	Asynch. Reset Pulse Duration	8	_	8	_	10	_	15	_	ns
tarr	_	Asynch. Reset to Clk↑ Recovery Time	8	_	8	_	10	_	15	_	ns
t spr	_	Synch. Preset to Clk↑ Recovery Time	10	_	10	_	10	_	12	_	ns

¹⁾ Refer to **Switching Test Conditions** section.

CAPACITANCE ($T_A = 25^{\circ}C$, f = 1.0 MHz)

SYMBOL	PARAMETER	MAXIMUM*	UNITS	TEST CONDITIONS
C	Input Capacitance	8	pF	$V_{CC} = 5.0V, V_{I} = 2.0V$
C _{I/O}	I/O Capacitance	8	pF	$V_{CC} = 5.0V, V_{I/O} = 2.0V$

^{*}Characterized but not 100% tested.

²⁾ Calculated from fmax with internal feedback. Refer to fmax Description section.

³⁾ Refer to fmax Description section.



ABSOLUTE MAXIMUM RATINGS(1)

Supply voltage V _{cc}	0.5 to +7V
Input voltage applied	2.5 to V _{cc} +1.0V
Off-state output voltage applied	2.5 to V _{cc} +1.0V
Storage Temperature	65 to 150°C
Ambient Temperature with	
Power Applied	55 to 125°C

1. Stresses above those listed under the "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress only ratings and functional operation of the device at these or at any other conditions above those indicated in the operational sections of this specification is not implied (while programming, follow the programming specifications).

RECOMMENDED OPERATING COND.

Commercial Devices:

DC ELECTRICAL CHARACTERISTICS

Over Recommended Operating Conditions (Unless Otherwise Specified)

PARAMETER	CONDITION	MIN.	TYP.3	MAX.	UNITS
Input Low Voltage		Vss - 0.5	_	0.8	V
Input High Voltage		2.0	_	Vcc+1	V
Input or I/O Low Leakage Current	$0V \le V_{IN} \le V_{IL}$ (MAX.)	_	_	-100	μА
Input or I/O High Leakage Current	$3.5V \le V$ in $\le V$ cc	_	_	10	μΑ
Output Low Voltage	$I_{OL} = MAX$. $V_{II} = V_{IL} \text{ or } V_{IH}$	_	_	0.5	V
Output High Voltage	$I_{OH} = MAX$. $Vin = V_{IL}$ or V_{IH}	2.4	_	_	V
Low Level Output Current		_	_	16	mA
High Level Output Current		_	_	-3.2	mA
Output Short Circuit Current	V cc = 5V V out = 0.5V Ta = 25°C	-50	_	-135	mA
	Input Low Voltage Input High Voltage Input or I/O Low Leakage Current Input or I/O High Leakage Current Output Low Voltage Output High Voltage Low Level Output Current High Level Output Current	Input Low Voltage Input High Voltage Input or I/O Low Leakage Current $0V \le V_{IN} \le V_{IL}$ (MAX.) Input or I/O High Leakage Current $3.5V \le V_{IN} \le V_{CC}$ Output Low Voltage $I_{OL} = MAX.$ $V_{IN} = V_{IL}$ or V_{IH} Output High Voltage $I_{OH} = MAX.$ $V_{IN} = V_{IL}$ or V_{IH} Low Level Output Current High Level Output Current	Input Low Voltage Vss − 0.5 Input High Voltage 2.0 Input or I/O Low Leakage Current $0V \le V_{IN} \le V_{IL}$ (MAX.) — Input or I/O High Leakage Current $3.5V \le V_{IN} \le V_{CC}$ — Output Low Voltage $I_{OL} = MAX$. $V_{IN} = V_{IL}$ or V_{IH} — Output High Voltage $I_{OH} = MAX$. $V_{IN} = V_{IL}$ or V_{IH} 2.4 Low Level Output Current — High Level Output Current —	Input Low Voltage Vss − 0.5 — Input High Voltage 2.0 — Input or I/O Low Leakage Current $0V \le V_{IN} \le V_{IL}$ (MAX.) — — Input or I/O High Leakage Current $3.5V \le V_{IN} \le V_{CC}$ — — Output Low Voltage IoL = MAX. Vin = VIL or VIH — — Output High Voltage IoH = MAX. Vin = VIL or VIH 2.4 — Low Level Output Current — — — High Level Output Current — — —	Input Low Voltage Vss − 0.5 — 0.8 Input High Voltage 2.0 — Vcc+1 Input or I/O Low Leakage Current $0V \le V_{IN} \le V_{IL}$ (MAX.) — — —100 Input or I/O High Leakage Current $3.5V \le V_{IN} \le V_{CC}$ — — 10 Output Low Voltage IoL = MAX. Vin = VIL or VIH — — 0.5 Output High Voltage IoH = MAX. Vin = VIL or VIH 2.4 — — Low Level Output Current — — — — — High Level Output Current — — — — — —

COMMERCIAL

Icc	Operating Power	V IL = 0.5V V IH = 3.0V	L -15/-20	_	75	115	mA
	Supply Current	f _{toggle} = 15MHz Outputs Open					

¹⁾ The leakage current is due to the internal pull-up on all pins. See **Input Buffer** section for more information.

²⁾ One output at a time for a maximum duration of one second. Vout = 0.5V was selected to avoid test problems caused by tester ground degradation. Characterized but not 100% tested.

³⁾ Typical values are at Vcc = 5V and TA = 25 °C



AC SWITCHING CHARACTERISTICS

Over Recommended Operating Condition	nmended Operating C	Conditions
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			CC	OM	CC	OM	
DADAMETED	TEST	DESCRIPTION	-1	15	-2	20	LINUTO
PARAMETER COND.1 DESCRIPTION		DESCRIPTION	MIN.	MAX.	MIN.	MAX.	UNITS
t pd	Α	Input or I/O to Combinatorial Output	_	15	_	20	ns
t co	А	Clock to Output Delay	_	10	_	12	ns
t cf ²	_	Clock to Feedback Delay	_	7	_	10	ns
t su	_	Setup Time, Input or Feedback before Clock↑	10	_	12	_	ns
t h	_	Hold Time, Input or Feedback after Clock↑	0	_	0	_	ns
	А	Maximum Clock Frequency with External Feedback, 1/(tsu +tco)	50	_	41.6	_	MHz
f max ³	А	Maximum Clock Frequency with Internal Feedback, 1/(tsu + tcf)	58.8	_	45.4	_	MHz
	А	Maximum Clock Frequency with No Feedback	62.5	_	62.5	_	MHz
t wh	_	Clock Pulse Duration, High	8	_	8	_	ns
twl	_	Clock Pulse Duration, Low	8	_	8	_	ns
t en	В	Input or I/O to Output Enabled	_	15	_	20	ns
t dis	С	Input or I/O to Output Disabled	_	15	_	20	ns
t ar	А	Input or I/O to Asynchronous Reset of Register	_	20	_	20	ns
t arw	_	Asynchronous Reset Pulse Duration	10	_	15	_	ns
t arr	_	Asynchronous Reset to Clock Recovery Time	15	_	15	_	ns
t spr	_	Synchronous Preset to Clock Recovery Time	10	_	12	_	ns

¹⁾ Refer to **Switching Test Conditions** section.

CAPACITANCE ($T_{\Delta} = 25^{\circ}C$, f = 1.0 MHz)

SYMBOL	PARAMETER	MAXIMUM*	UNITS	TEST CONDITIONS
C _I	Input Capacitance	8	pF	$V_{CC} = 5.0V, V_{I} = 2.0V$
C _{I/O}	I/O Capacitance	10	pF	$V_{CC} = 5.0V, V_{I/O} = 2.0V$

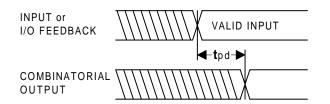
^{*}Characterized but not 100% tested.

²⁾ Calculated from fmax with internal feedback. Refer to fmax Description section.

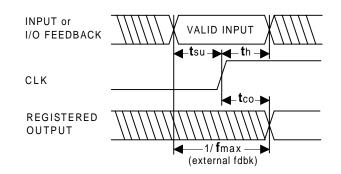
³⁾ Refer to **fmax Description** section.



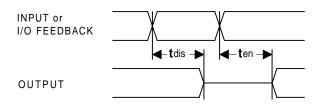
SWITCHING WAVEFORMS



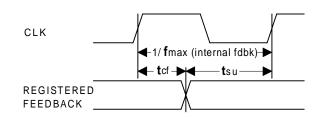
Combinatorial Output



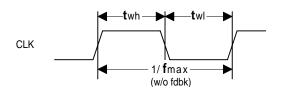
Registered Output



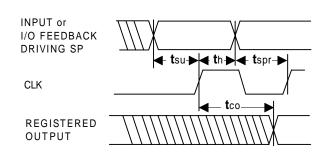
Input or I/O to Output Enable/Disable



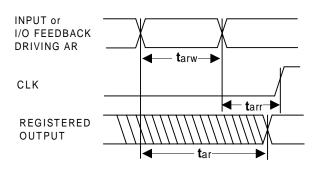
fmax with Feedback



Clock Width



Synchronous Preset

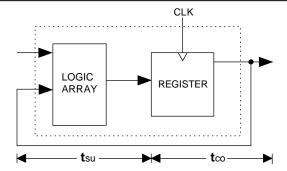


Asynchronous Reset



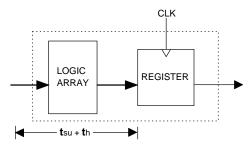


fmax DESCRIPTIONS



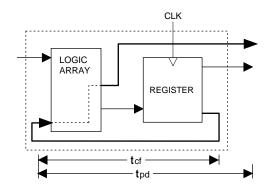
fmax with External Feedback 1/(tsu+tco)

Note: fmax with external feedback is calculated from measured tsu and tco.



fmax with No Feedback

Note: fmax with no feedback may be less than 1/(twh + twl). This is to allow for a clock duty cycle of other than 50%.



fmax with Internal Feedback 1/(tsu+tcf)

Note: tcf is a calculated value, derived by subtracting tsu from the period of fmax w/internal feedback (tcf = 1/fmax - tsu). The value of tcf is used primarily when calculating the delay from clocking a register to a combinatorial output (through registered feedback), as shown above. For example, the timing from clock to a combinatorial output is equal to tcf + tpd.

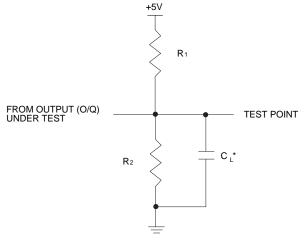
SWITCHING TEST CONDITIONS

Input Pulse Levels	GND to 3.0V	
Input Rise and	-7/-10	2ns 10% – 90%
Fall Times	-15/-20	3ns 10% – 90%
Input Timing Reference	1.5V	
Output Timing Refere	1.5V	
Output Load	See Figure	

3-state levels are measured 0.5V from steady-state active level.

Output Load Conditions (see figure)

output I oud out attions (out inguity)							
t Condition	R ₁	R ₂	CL				
	300Ω	390Ω	50pF				
Active High	∞	390Ω	50pF				
Active Low	300Ω	390Ω	50pF				
Active High	∞	390Ω	5pF				
Active Low	300Ω	390Ω	5pF				
	Active High Active Low Active High	$\begin{array}{c c} \textbf{t Condition} & \textbf{R}_1 \\ & 300\Omega \\ \hline & \text{Active High} & \infty \\ \hline & \text{Active Low} & 300\Omega \\ \hline & \text{Active High} & \infty \\ \hline \end{array}$	$\begin{array}{c cccc} \textbf{t Condition} & & \textbf{R}_1 & & \textbf{R}_2 \\ & & 300\Omega & 390\Omega \\ & & & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & & \\ & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & &$				



 $^{*}C_{L}$ INCLUDES TEST FIXTURE AND PROBE CAPACITANCE



ELECTRONIC SIGNATURE

An electronic signature is provided in every GAL18V10 device. It contains 64 bits of reprogrammable memory that can contain user-defined data. Some uses include user ID codes, revision numbers, or inventory control. The signature data is always available to the user independent of the state of the security cell.

SECURITY CELL

A security cell is provided in every GAL18V10 device to prevent unauthorized copying of the array patterns. Once programmed, this cell prevents further read access to the functional bits in the device. This cell can only be erased by re-programming the device, so the original configuration can never be examined once this cell is programmed. The Electronic Signature is always available to the user, regardless of the state of this control cell.

LATCH-UP PROTECTION

GAL18V10 devices are designed with an on-board charge pump to negatively bias the substrate. The negative bias is of sufficient magnitude to prevent input undershoots from causing the circuitry to latch. Additionally, outputs are designed with n-channel pullups instead of the traditional p-channel pullups to eliminate any possibility of SCR induced latching.

DEVICE PROGRAMMING

GAL devices are programmed using a Lattice Semiconductorapproved Logic Programmer, available from a number of manufacturers (see the the GAL Development Tools section). Complete programming of the device takes only a few seconds. Erasing of the device is transparent to the user, and is done automatically as part of the programming cycle.

OUTPUT REGISTER PRELOAD

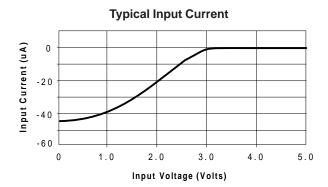
When testing state machine designs, all possible states and state transitions must be verified in the design, not just those required in the normal machine operations. This is because certain events may occur during system operation that throw the logic into an illegal state (power-up, line voltage glitches, brown-outs, etc.). To test a design for proper treatment of these conditions, a way must be provided to break the feedback paths, and force any desired (i.e., illegal) state into the registers. Then the machine can be sequenced and the outputs tested for correct next state conditions.

The GAL18V10 device includes circuitry that allows each registered output to be synchronously set either high or low. Thus, any present state condition can be forced for test sequencing. If necessary, approved GAL programmers capable of executing test vectors perform output register preload automatically.

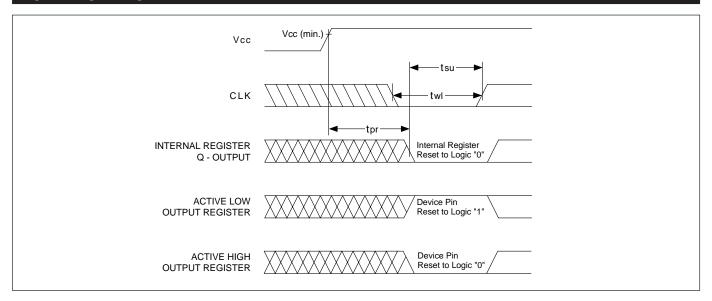
INPUT BUFFERS

GAL18V10 devices are designed with TTL level compatible input buffers. These buffers have a characteristically high impedance, and present a much lighter load to the driving logic than bipolar TTL devices.

The input and I/O pins also have built-in active pull-ups. As a result, floating inputs will float to a TTL high (logic 1). However, Lattice Semiconductor recommends that all unused inputs and tri-stated I/O pins be connected to an adjacent active input, Vcc, or ground. Doing so will tend to improve noise immunity and reduce Icc for the device.



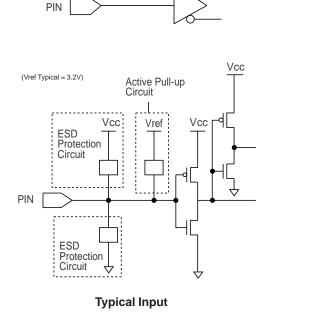
POWER-UP RESET

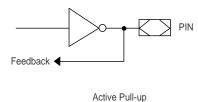


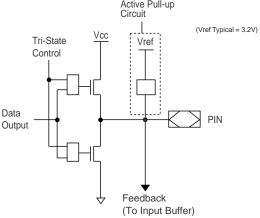
Circuitry within the GAL18V10 provides a reset signal to all registers during power-up. All internal registers will have their Q outputs set low after a specified time (tpr, $1\mu s$ MAX). As a result, the state on the registered output pins (if they are enabled) will be either high or low on power-up, depending on the programmed polarity of the output pins. This feature can greatly simplify state machine design by providing a known state on power-up. Because of the asynchronous nature of system power-up, some

conditions must be met to provide a valid power-up reset of the device. First, the Vcc rise must be monotonic. Second, the clock input must be at static TTL level as shown in the diagram during power up. The registers will reset within a maximum of tpr time. As in normal system operation, avoid clocking the device until all input and feedback path setup times have been met. The clock must also meet the minimum pulse width requirements.

INPUT/OUTPUT EQUIVALENT SCHEMATICS





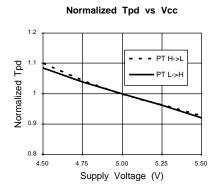


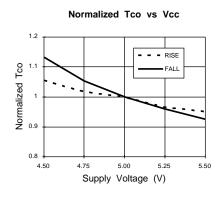
Typical Output

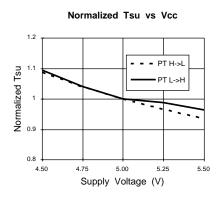


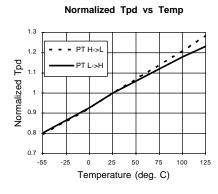


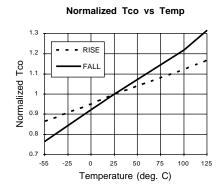
GAL18V10B: TYPICAL AC AND DC CHARACTERISTIC DIAGRAMS

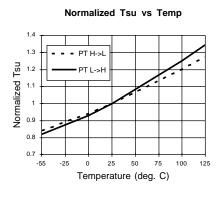


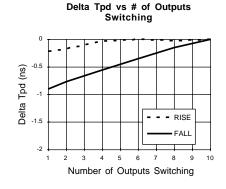


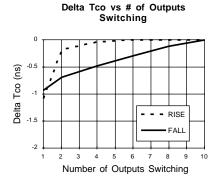


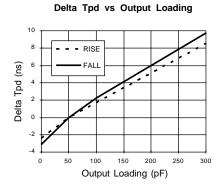


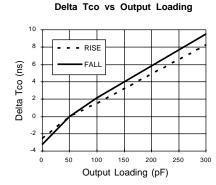
















GAL18V10B: TYPICAL AC AND DC CHARACTERISTIC DIAGRAMS

